Is Now Part of

ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at
www.onsemi.com

FAIRCHILD SEMICONDUCTOR®

November 2013

FGH30T65UPDT

650V, 30A Field Stop Trench IGBT

Features

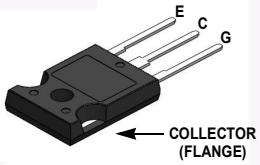
- Maximum Junction Temperature : T_J = 175°C
- Positive Temperaure Co-efficient for Easy Parallel Operating
- High Current Capability
- Low Saturation Voltage: $V_{CE(sat)}$ = 1.65 V (Typ.) @ I_C = 30 A
- 100% of Parts Tested $I_{LM(2)}$
- High Input Impedance
- Tightened Parameter Distribution
- RoHS Compliant
- Short Circuit Ruggedness > 5 us @ 25°C

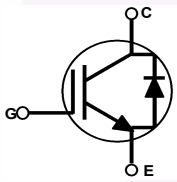
General Description

Using novel field stop trench IGBT technology, Fairchild's new series of field stop trench IGBTs offer the optimum performance for solar inverter , UPS and digital power generator where low conduction and switching losses are essential.

Applications

- Solar Inverter, UPS, Digital Power Generator





Absolute Maximum Ratings

Symbol	Description		Ratings	Unit
V_{CES}	Collector to Emitter Voltage		650	V
V_{GES}	Gate to Emitter Voltage		± 20	V
	Transient Gate to Emitter Voltage		± 25	V
I_C	Collector Current	@ T_C = 25°C	60	A
	Collector Current	@ T_C = 100°C	30	A
$I_{CM(1)}$	Pulsed Collector Current		90	A
$I_{LM(2)}$	Clamped Inductive Load Current		90	A
I_F	Diode Forward Current	@ T_C = 25°C	60	A
	Diode Forward Current	@ T_C = 100°C	30	A
$I_{FM(1)}$	Pulsed Diode Maximum Forward Current		150	A
P_D	Maximum Power Dissipation	@ T_C = 25°C	250	W
	Maximum Power Dissipation	@ T_C = 100°C	125	W
SCWT	Short Circuit Withstand Time	@ T_C = 25°C	5	us
T_J	Operating Junction Temperature		-55 to +175	°C
T_{stg}	Storage Temperature Range		-55 to +175	°C
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C

Notes:
1: Repetitive rating: Pulse width limited by max. junction temperature
2: I_C = 90 A, V_{CC} = 400 V, R_g = 20 Ω

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$(IGBT)	Thermal Resistance, Junction to Case	-	0.60	°C/W
$R_{\theta JC}$(Diode)	Thermal Resistance, Junction to Case	-	1.2	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	-	40	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FGH30T65UPD_F155	FGH30T65UPD	TO-247 G03	Tube	N/A	N/A	30

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{CES}	Collector to Emitter Breakdown Voltage	V_{GE} = 0 V, I_C = 1 mA	650	-	-	V
$\frac{\Delta BV_{CES}}{\Delta T_J}$	Temperature Coefficient of Breakdown Voltage	V_{GE} = 0 V, I_C = 250 uA	-	0.65	-	V/°C
I_{CES}	Collector Cut-Off Current	V_{CE} = V_{CES}, V_{GE} = 0 V	-	-	250	μA
I_{GES}	G-E Leakage Current	V_{GE} = V_{GES}, V_{CE} = 0 V	-	-	±400	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	I_C = 30 mA, V_{CE} = V_{GE}	4.0	6.0	7.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	I_C = 30 A, V_{GE} = 15 V	-	1.65	2.3	V
		I_C = 30 A, V_{GE} = 15 V, T_C = 175°C	-	2.1	-	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	V_{CE} = 30 V, V_{GE} = 0 V, f = 1 MHz	-	2280	-	pF
C_{oes}	Output Capacitance		-	85	-	pF
C_{res}	Reverse Transfer Capacitance		-	40	-	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 400 V, I_C = 30 A, R_G = 8 Ω, V_{GE} = 15 V, Inductive Load, T_C = 25°C	-	22	-	ns
t_r	Rise Time		-	26	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	139	-	ns
t_f	Fall Time		-	18	-	ns
E_{on}	Turn-On Switching Loss		-	0.76	-	mJ
E_{off}	Turn-Off Switching Loss		-	0.40	-	mJ
E_{ts}	Total Switching Loss		-	1.16	-	mJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 400 V, I_C = 30 A, R_G = 8 Ω, V_{GE} = 15V, Inductive Load, T_C = 175°C	-	22	-	ns
t_r	Rise Time		-	30	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	151	-	ns
t_f	Fall Time		-	19	-	ns
E_{on}	Turn-On Switching Loss		-	1.20	-	mJ
E_{off}	Turn-Off Switching Loss		-	0.53	-	mJ
E_{ts}	Total Switching Loss		-	1.73	-	mJ
Tsc	Short Circuit Withstand Time	V_{GE} = 15 V, V_{CC} ≤ 400 V, Rg = 10 Ω	5	-	-	us
Q_g	Total Gate Charge	V_{CE} = 400 V, I_C = 30 A, V_{GE} = 15 V	-	155	-	nC
Q_{ge}	Gate to Emitter Charge		-	21	-	nC
Q_{gc}	Gate to Collector Charge		-	91	-	nC

Electrical Characteristics of the Diode T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Typ.	Max	Unit
V_{FM}	Diode Forward Voltage	I_F = 30 A	T_C = 25°C	-	2.3	3.0	V
			T_C = 175°C	-	1.9	-	
E_{rec}	Reverse Recovery Energy	I_F = 30 A, di_F/dt = 200 A/μs	T_C = 175°C	-	35	-	uJ
t_{rr}	Diode Reverse Recovery Time		T_C = 25°C	-	33	43	ns
			T_C = 175°C	-	148		
Q_{rr}	Diode Reverse Recovery Charge		T_C = 25°C	-	57	80	nC
			T_C = 175°C	-	560		

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

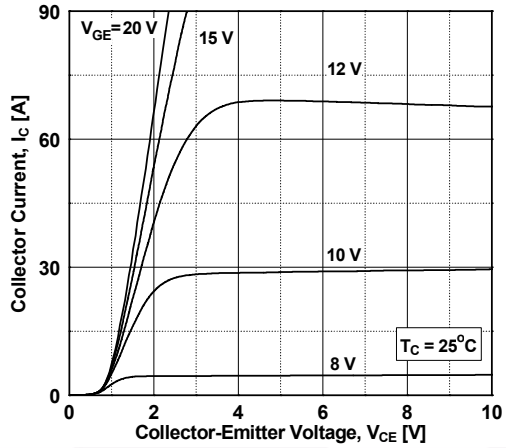


Figure 2. Typical Output Characteristics

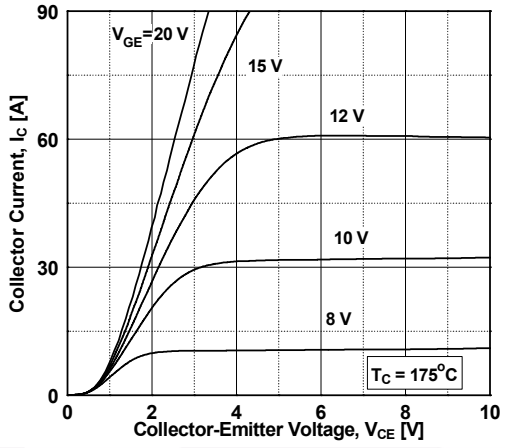


Figure 3. Typical Saturation Voltage Characteristics

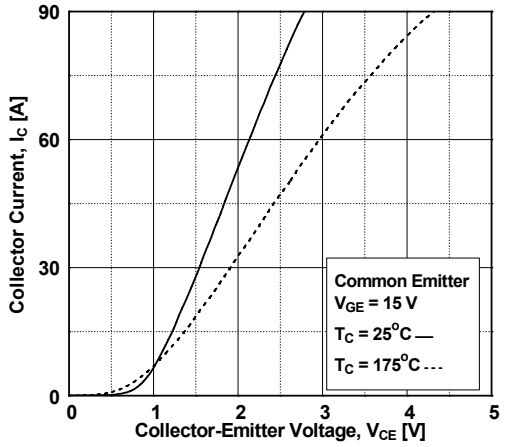


Figure 4. Saturation Voltage vs. Case Temperature at Variant Current Leve

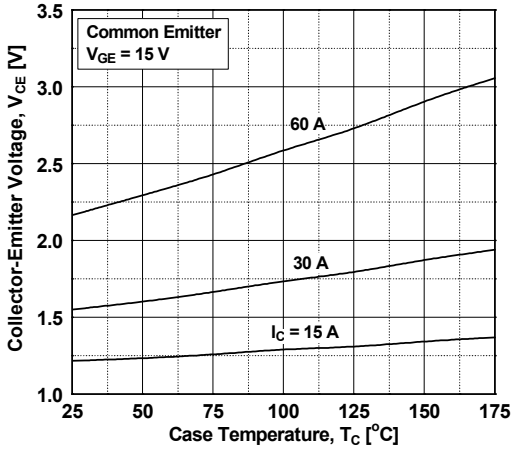


Figure 5. Saturation Voltage vs. V_{GE}

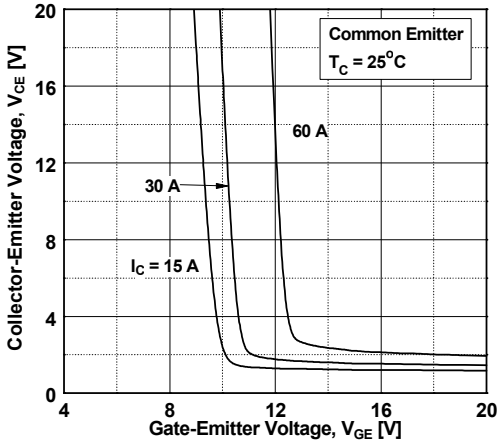
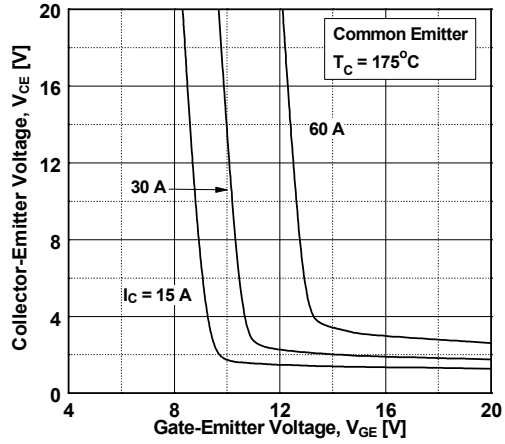


Figure 6. Saturation Voltage vs. V_{GE}



Typical Performance Characteristics

Figure 7. Capacitance Characteristic

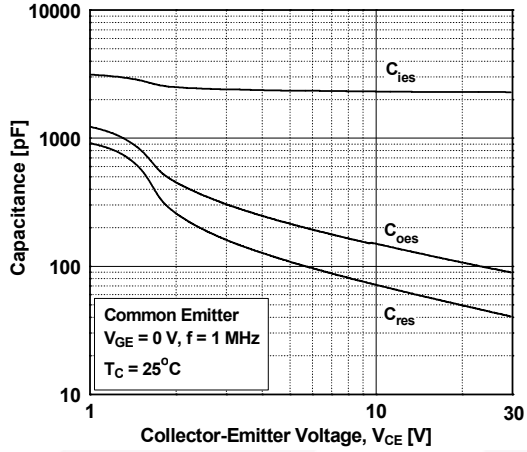


Figure 8. Gate charge Characteristics

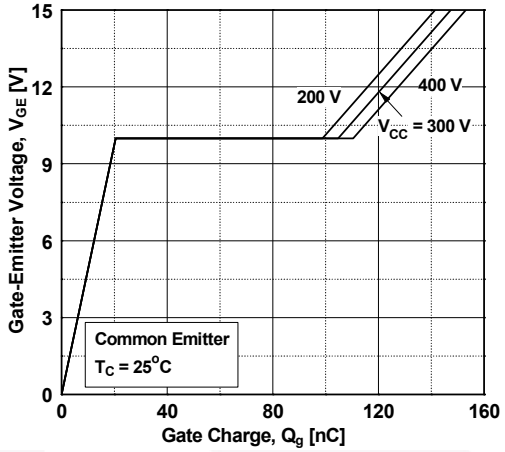


Figure 9. Turn-on Characteristics vs. Gate Resistance

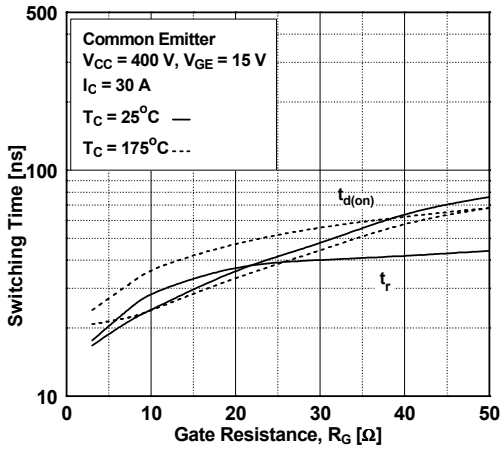


Figure 10. Turn-off Characteristics vs. Gate Resistance

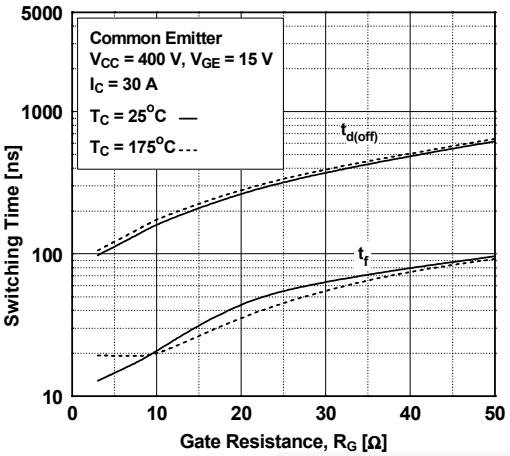


Figure 11. Switching Loss vs. Gate Resistance

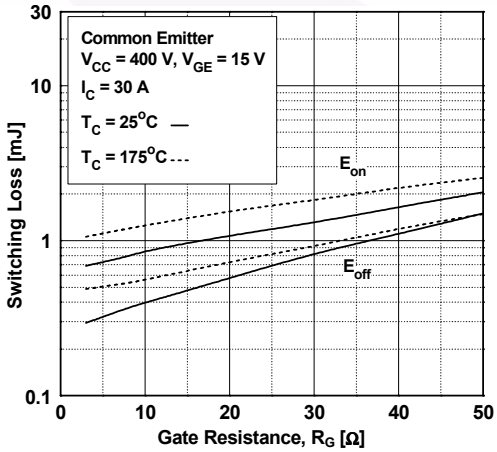
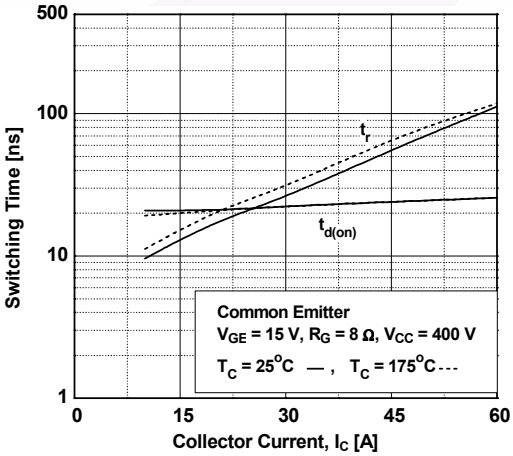


Figure 12. Turn-on Characteristics vs. Collector Current



Typical Performance Characteristics

Figure 13. Turn-off Characteristics vs. Collector Current

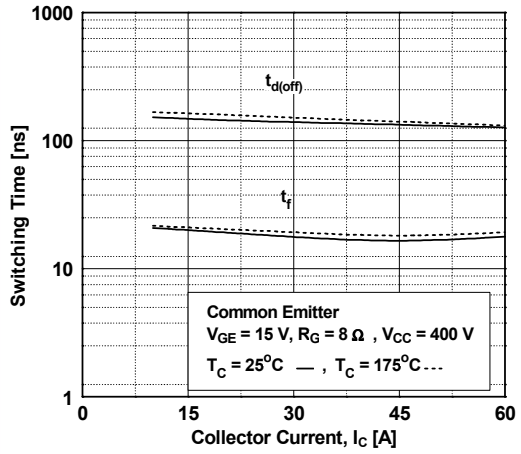


Figure 14. Switching Loss vs. Collector Current

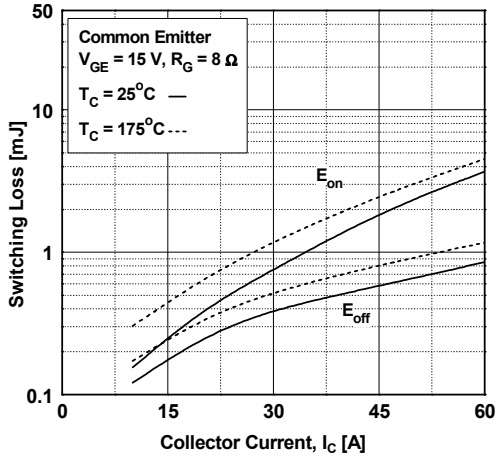


Figure 15. Load Current vs. Frequency

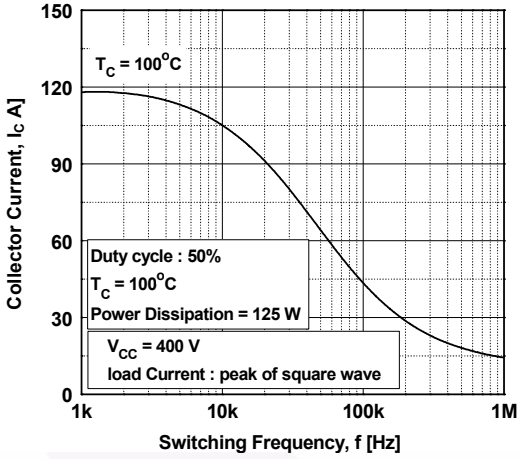


Figure 16. SOA Characteristics

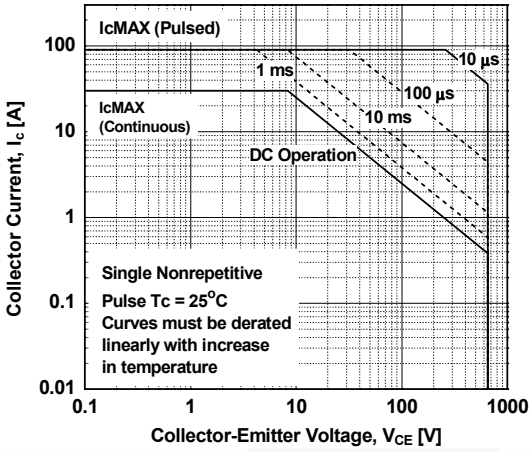


Figure 17. Forward Characteristics

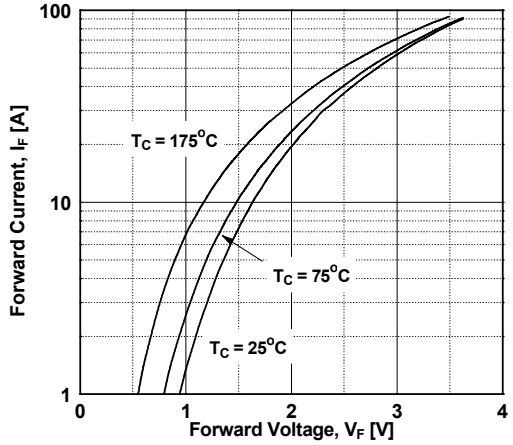
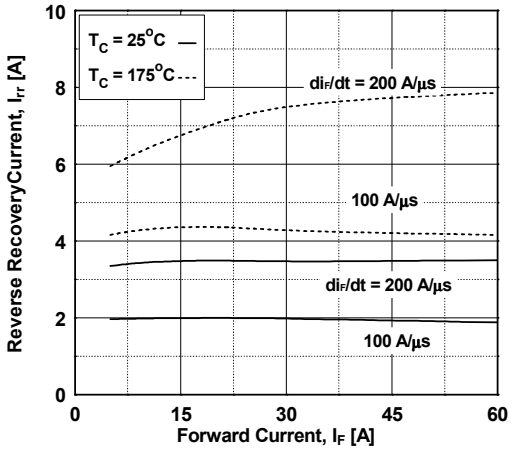


Figure 18. Reverse Revovery Current



Typical Performance Characteristics

Figure 19. Reverse Recovery Time

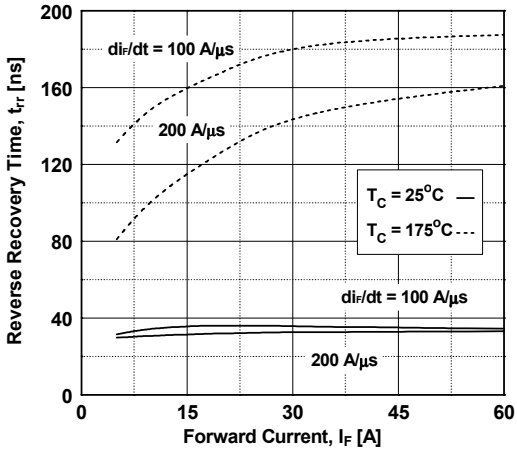


Figure 20. Stored Charge

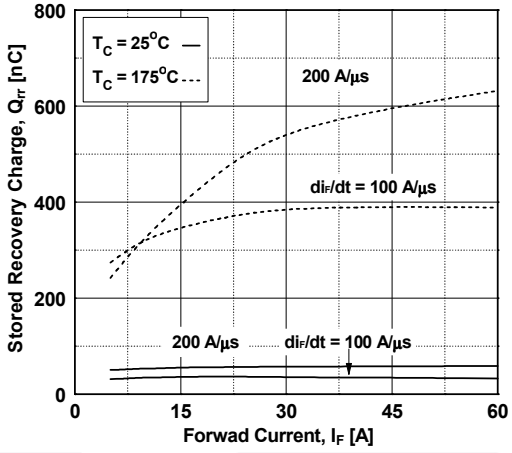


Figure 21. Transient Thermal Impedance of IGBT

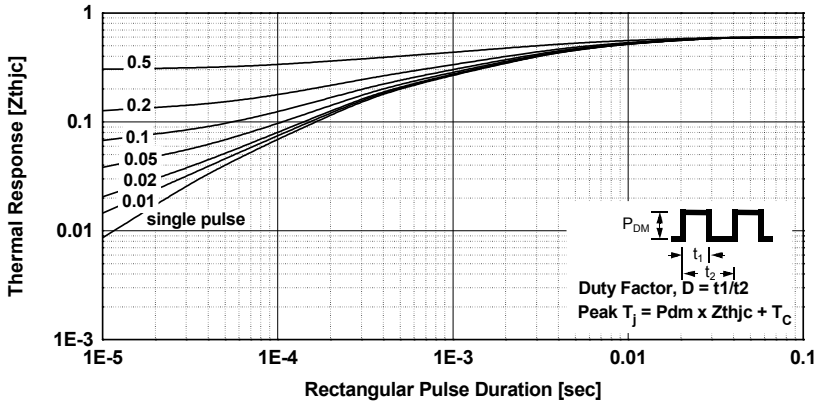
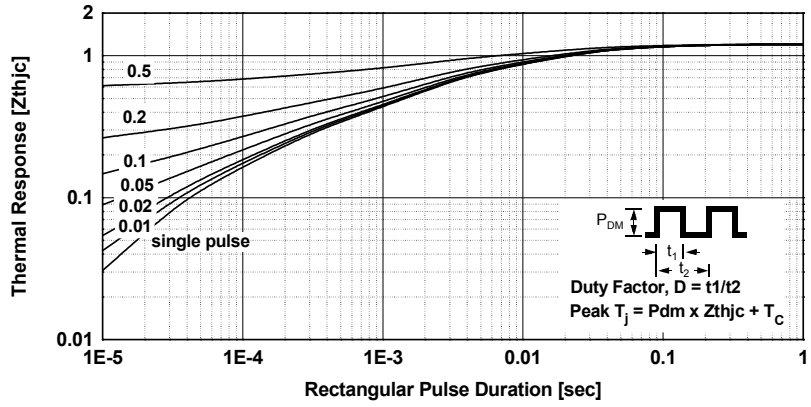
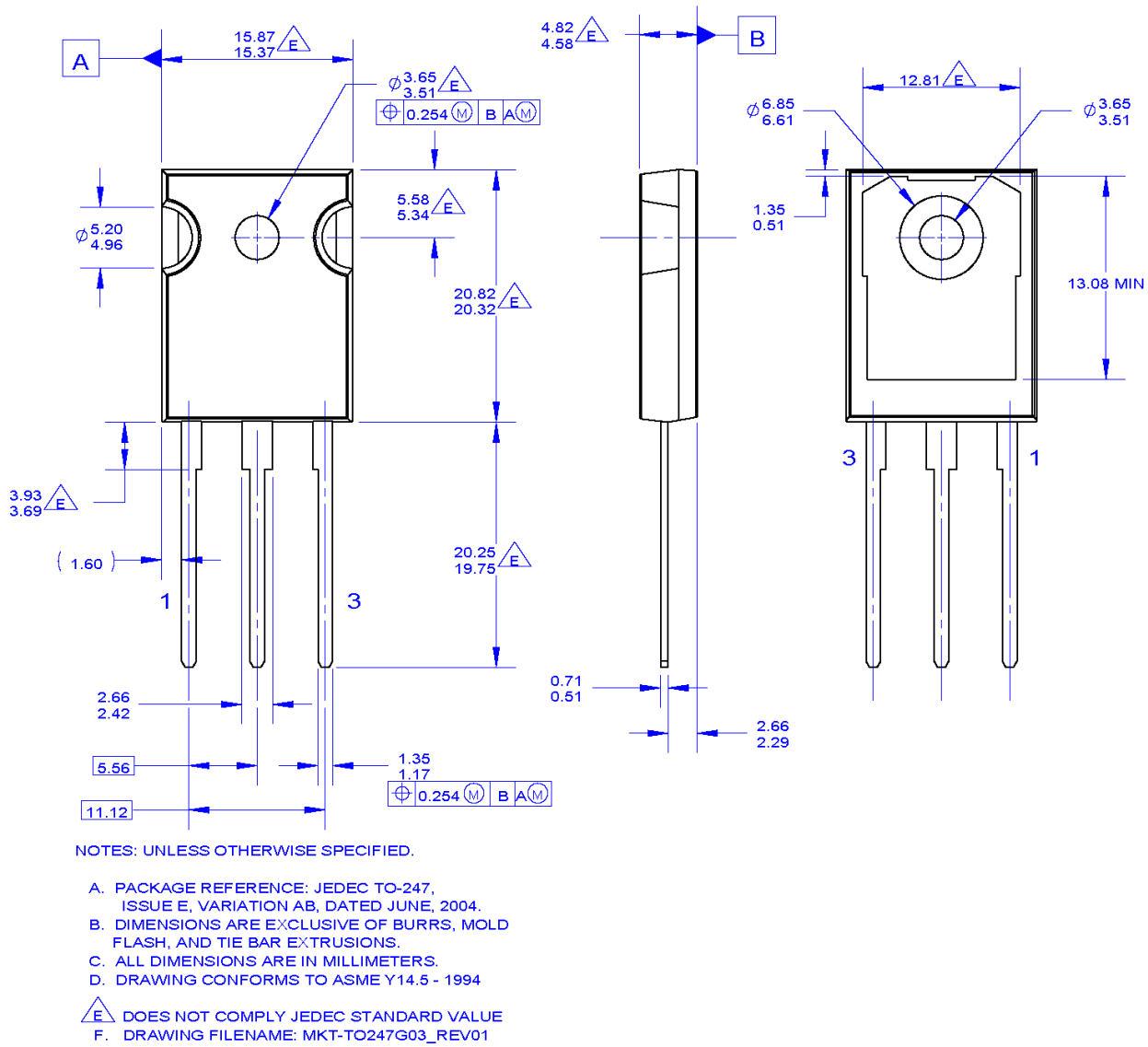


Figure 22. Transient Thermal Impedance of Diode



Mechanical Dimensions



NOTES: UNLESS OTHERWISE SPECIFIED.

A. PACKAGE REFERENCE: JEDEC TO-247, ISSUE E, VARIATION AB, DATED JUNE, 2004.
B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
C. ALL DIMENSIONS ARE IN MILLIMETERS.
D. DRAWING CONFORMS TO ASME Y14.5 - 1994

E DOES NOT COMPLY JEDEC STANDARD VALUE
F. DRAWING FILENAME: MKT-TO247G03_REV01

Figure 23. TO247, Molded, 3-Lead, JEDEC AB Long Lead

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TO247-0A3

Dimensions in Millimeters

FAIRCHILD SEMICONDUCTOR®

TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower™
AX-CAP®*
BitSiC™
Build it Now™
CorePLUS™
CorePOWER™
CROSSVOLT™
CTL™
Current Transfer Logic™
DEUXPEED®
Dual Cool™
EcoSPARK®
EfficentMax™
ESBC™
Fairchild®
Fairchild Semiconductor®
FACT Quiet Series™
FACT®
FAST®
FastvCore™
FETBench™
FPS™
F-PFS™
FRFET®
Global Power Resource℠
GreenBridge™
Green FPS™
Green FPS™ e-Series™
G*max*™
GTO™
IntelliMAX™
ISOPLANAR™
Marking Small Speakers Sound Louder and Better™
MegaBuck™
MICROCOUPLER™
MicroFET™
MicroPak™
MicroPak2™
MillerDrive™
MotionMax™
mWSaver®
OptoHiT™
OPTOLOGIC®
OPTOPLANAR®
PowerTrench®
PowerXS™
Programmable Active Droop™
QFET®
QS™
Quiet Series™
RapidConfigure™
Saving our world, 1mW/W/kW at a time™
SignalWise™
SmartMax™
SMART START™
Solutions for Your Success™
SPM®
STEALTH™
SuperFET®
SuperSOT™-3
SuperSOT™-6
SuperSOT™-8
SupreMOS®
SyncFET™
Sync-Lock™
SYSTEM GENERAL ®*
TinyBoost®
TinyBuck®
TinyCalc™
TinyLogic®
TINYOPTO™
TinyPower™
TinyPWM™
TinyWire™
TranSiC™
TriFault Detect™
TRUECURRENT®*
µSerDes™
SerDes™
UHC®
Ultra FRFET™
UniFET™
VCX™
VisualMax™
VoltagePlus™
XS™

*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS
Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I66

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Fairchild Semiconductor:
FGH30T65UPDT_F155